IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant:

Yeo, et al.

Docket No.:

TSM03-0511

Filed:

Herewith

Examiner:

TBD

Serial No.:

TBD

Art Unit:

TBD

For:

Multiple-Gate Transistors Formed on Bulk Substrates

Mail Stop: Patent Application Commissioner for Patents P. O. Box 1450 Alexandria, VA 22313-1450

INFORMATION DISCLOSURE STATEMENT

Dear Sir:

Applicant wishes to bring to the attention of the Patent and Trademark Office the information noted on the enclosed form PTO/SB/08A that may be considered material to the examination of the above-identified application.

Pursuant to 37 CFR 1.98(a)(2)(i), as amended, copies of U.S. Patents cited are not being submitted. However, Applicant has included copies of the non-patent literature.

No fee is due at this time, as this Information Disclosure Statement is being filed concurrently with the patent application.

September 24, 2003

Date

Respectfully submitted,

2003 Ira S. Matsil
Attorney for Applicant

Reg. No. 35,272

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Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT						Complete if Known					
						Application Number		TBD	TBD		
						Filing Date		Herew	Herewith		
						First Named Inventor		Yeo, et al.			
					Art Unit TBD						
(use as many sheets as necessary)						Examiner Name TBD		TBD			
Sheet	et 1 of 1			Attorney Docket Number TS		TSM0	TSM03-0511				
				U.S. P	ATENT	DOCUM	ENTS				
Examiner Initials*	Cite	Document Nur	Publication	Publication Date MM-DD-YYYY		Name of Patentee or Applicant of Cited Document		Pages, Columns, Lines Relevant Passages or F Figures Appear			
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Examiner	Cite	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the								2 ا	!
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	Н	HUANG, X., et al. "Sub-50 nm P-Channel FinFET," IEEE Transactions on Electron Devices, Vol. 48, No. 5 (May 2001) pp. 880-886.									
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application. Confidentiality is governed by 35 U.S.C. 122 and 37 CFR 1.14. This collection is estimated to take 2 hours to complete, including gathering, preparing, and submitting the completed application form to the USPTO. Time will vary depending upon the individual case. Any comments on the amount of time you require to complete this form and/or suggestions for reducing this burden, should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, U.S. Department of Commerce, P.O. Box 1450, Alexandria, VA 22313-1450. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.

^{*}EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. Applicant's unique citation designation number (optional). See Kinds Codes of USPTO Patent Documents at www.uspto.gov or MPEP 901.04. Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. Applicant is to place a check mark here if English language Translation is attached.

This collection of information is required by 37 CFR 1.97 and 1.98. The information is required to obtain or retain a benefit by the public which is to file (and by the USPTO to process) an